Quad Analog Switch/ Multiplexer/Demultiplexer High-Performance Silicon-Gate CMOS

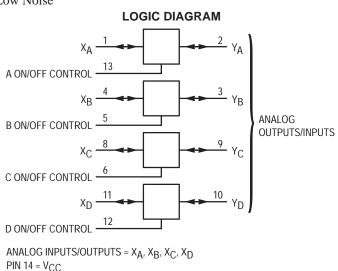
The MC74LVXT4066 utilizes silicon-gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF-channel leakage current. This bilateral switch/multiplexer/demultiplexer controls analog and digital voltages that may vary across the full power-supply range (from VCC to GND).

The LVXT4066 is identical in pinout to the metal–gate CMOS MC14066 and the high–speed CMOS HC4066A. Each device has four independent switches. The device has been designed so that the ON resistances (R_{ON}) are much more linear over input voltage than R_{ON} of metal–gate CMOS analog switches.

The ON/OFF control inputs are compatible with standard LSTTL outputs. The input protection circuitry on this device allows overvoltage tolerance on the ON/OFF control inputs, allowing the device to be used as a logic–level translator from 3.0V CMOS logic to 5.0V CMOS Logic or from 1.8V CMOS logic to 3.0V CMOS Logic while operating at the higher–voltage power supply.

The MC74LVXT4066 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74LVXT4066 to be used to interface 5V circuits to 3V circuits.

- Fast Switching and Propagation Speeds
- High ON/OFF Output Voltage Ratio
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Wide Power–Supply Voltage Range $(V_{CC} GND) = 2.0$ to 6.0 Volts
- Analog Input Voltage Range $(V_{CC} GND) = 2.0$ to 6.0 Volts
- Improved Linearity and Lower ON Resistance over Input Voltage than the MC14016 or MC14066
- Low Noise





http://onsemi.com





14-LEAD SOIC D SUFFIX CASE 751A 14-LEAD TSSOP DT SUFFIX CASE 948G

PIN CONNECTION AND MARKING DIAGRAM (Top View)

X _A Y _A Y _B X _B B ON/OFF	1 • 2 3 4 5	14 13 12 11 10	V _{CC} A ON/OFF CONTROL D ON/OFF CONTROL X _D
CONTROL C ON/OFF CONTROL GND	6	9	Y _C X _C

For detailed package marking information, see the Marking Diagram section on page 10 of this data sheet.

FUNCTION TABLE

On/Off Control	State of
Input	Analog Switch
L	Off
H	On

ORDERING INFORMATION

Device	Package	Shipping
MC74LVXT4066D	SOIC	55 Units/Rail
MC74LVXT4066DR2	SOIC	2500 Units/Reel
MC74LVXT4066DT	TSSOP	96 Units/Rail
MC74LVXT4066DTR2	TSSOP	2500 Units/Reel

PIN 7 = GND

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	Positive DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
VIS	Analog Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{in}	Digital Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I	DC Current Into or Out of Any Pin	-20	mA
PD	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C

^{*}Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
VCC	Positive DC Supply Voltage (Referenced to GND)	2.0	5.5	V
VIS	Analog Input Voltage (Referenced to GND)	GND	Vcc	V
V _{in}	Digital Input Voltage (Referenced to GND)	GND	Vcc	V
V _{IO} *	Static or Dynamic Voltage Across Switch	_	1.2	V
TA	Operating Temperature, All Package Types		+ 85	°C
t _r , t _f	Input Rise and Fall Time, ON/OFF Control			ns/V
	Inputs (Figure 10) $ V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} $ $ V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V} $	0	100	
	$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	20	

^{*}For voltage drops across the switch greater than 1.2 V (switch on), excessive V_{CC} current may be drawn; i.e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

DC ELECTRICAL CHARACTERISTIC Digital Section (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High-Level Voltage ON/OFF Control Inputs (Note 1)	R _{on} = Per Spec	3.0 4.5 5.5	1.2 2.0 2.0	1.2 2.0 2.0	1.2 2.0 2.0	V
VIL	Maximum Low–Level Voltage ON/OFF Control Inputs (Note 1)	R _{on} = Per Spec	3.0 4.5 5.5	0.53 0.8 0.8	0.53 0.8 0.8	0.53 0.8 0.8	V
l _{in}	Maximum Input Leakage Current ON/OFF Control Inputs	V _{in} = V _{CC} or GND	5.5	± 0.1	± 1.0	± 1.0	μА
ICC	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND V _{IO} = 0 V	5.5	4.0	40	160	μΑ

^{1.} Specifications are for design target only. Not final specification limits.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open. I/O pins must be connected to a properly terminated line or bus.

[†]Derating — SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS Analog Section (Voltages Referenced to GND)

				Guaranteed Limit		mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
R _{on}	Maximum "ON" Resistance	$V_{\text{in}} = V_{\text{IH}}$ $V_{\text{IS}} = V_{\text{CC}}$ to GND $I_{\text{S}} \le 2.0$ mA (Figures 1, 2)	2.0† 3.0 4.5 5.5	— 40 25 20	— 45 28 25	— 50 35 30	Ω
		$V_{\text{in}} = V_{\text{IH}}$ $V_{\text{IS}} = V_{\text{CC}}$ or GND (Endpoints) $I_{\text{S}} \le 2.0$ mA (Figures 1, 2)	2.0 3.0 4.5 5.5	— 30 25 20	— 35 28 25	— 40 35 30	
ΔR _{on}	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$\begin{aligned} &V_{\text{IR}} = V_{\text{IH}} \\ &V_{\text{IS}} = 1/2 \left(V_{\text{CC}} - \text{GND} \right) \\ &I_{\text{S}} \leq 2.0 \text{ mA} \end{aligned}$	3.0 4.5 5.5	15 10 10	20 12 12	25 15 15	Ω
l _{off}	Maximum Off–Channel Leakage Current, Any One Channel	V _{IO} = V _{IL} V _{IO} = V _{CC} or GND Switch Off (Figure 3)	5.5	0.1	0.5	1.0	μА
I _{on}	Maximum On–Channel Leakage Current, Any One Channel	V _{in} = V _{IH} V _{IS} = V _{CC} or GND (Figure 4)	5.5	0.1	0.5	1.0	μΑ

 $[\]dagger$ At supply voltage (V_{CC}) approaching 2 V the analog switch-on resistance becomes extremely non-linear. Therefore, for low-voltage operation, it is recommended that these devices only be used to control digital signals.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50$ pF, ON/OFF Control Inputs: $t_f = t_f = 6$ ns)

			Guaranteed Limit			
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
tPLH, tPHL	Maximum Propagation Delay, Analog Input to Analog Output (Figures 8 and 9)	2.0 3.0 4.5 5.5	4.0 3.0 1.0 1.0	6.0 5.0 2.0 2.0	8.0 6.0 2.0 2.0	ns
tPLZ, tPHZ	Maximum Propagation Delay, ON/OFF Control to Analog Output (Figures 10 and 11)	2.0 3.0 4.5 5.5	30 20 15 15	35 25 18 18	40 30 22 20	ns
tPZL, tPZH	Maximum Propagation Delay, ON/OFF Control to Analog Output (Figures 10 and 1 1)	2.0 3.0 4.5 5.5	20 12 8.0 8.0	25 14 10 10	30 15 12 12	ns
С	Maximum Capacitance ON/OFF Control Input Control Input = GND Analog I/O Feedthrough	_ _ _	10 35 1.0	10 35 1.0	10 35 1.0	pF
			Typical	@ 25°C, V _C (c = 5.0 V	

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Switch) (Figure 13)*	15	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

Symbol	Parameter	Test Conditions	V _{CC}	Limit* 25°C	Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response (Figure 5)	f_{in} = 1 MHz Sine Wave Adjust f_{in} Voltage to Obtain 0 dBm at VOS Increase f_{in} Frequency Until dB Meter Reads – 3 dB R_{L} = 50 Ω , C_{L} = 10 pF		150 160	MHz
_	Off–Channel Feedthrough Isolation (Figure 6)	$\begin{split} f_{\text{in}} &\equiv \text{Sine Wave} \\ \text{Adjust } f_{\text{in}} &\text{ Voltage to Obtain 0 dBm at V}_{\text{IS}} \\ f_{\text{in}} &= 10 \text{ kHz}, \text{ R}_{\text{L}} = 600 \ \Omega, \text{ C}_{\text{L}} = 50 \text{ pF} \end{split}$	4.5 5.5	- 50 - 50	dB
		f_{in} = 1.0 MHz, R_L = 50 Ω , C_L = 10 pF	4.5 5.5	- 37 - 37	
_	Feedthrough Noise, Control to Switch (Figure 7)	$V_{in} \leq$ 1 MHz Square Wave ($t_r = t_f = 3 \text{ ns}$) Adjust R _L at Setup so that I _S = 0 A R _L = 600 Ω , C _L = 50 pF	4.5 5.5	100 200	mVpp
		R_L = 10 kΩ, C_L = 10 pF	4.5 5.5	50 100	
_	Crosstalk Between Any Two Switches (Figure 12)	$ \begin{aligned} f_{\text{in}} &\equiv \text{Sine Wave} \\ \text{Adjust } f_{\text{in}} &\text{ Voltage to Obtain 0 dBm at V}_{\text{IS}} \\ f_{\text{in}} &= 10 \text{ kHz}, \text{ R}_{\text{L}} = 600 \ \Omega, \text{ C}_{\text{L}} = 50 \text{ pF} \end{aligned} $	4.5 5.5	- 70 - 70	dB
		f_{in} = 1.0 MHz, R_L = 50 Ω , C_L = 10 pF	4.5 5.5	- 80 - 80	
THD	Total Harmonic Distortion (Figure 14)	f_{in} = 1 kHz, R _L = 10 k Ω , C _L = 50 pF THD = THD _{Measured} - THD _{Source} V _{IS} = 4.0 Vpp sine wave V _{IS} = 5.0 Vpp sine wave		0.10 0.06	%

^{*}Guaranteed limits not tested. Determined by design and verified by qualification.

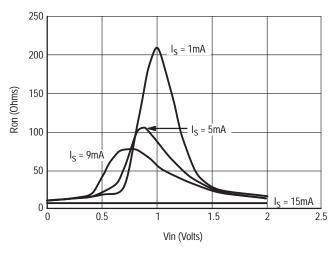
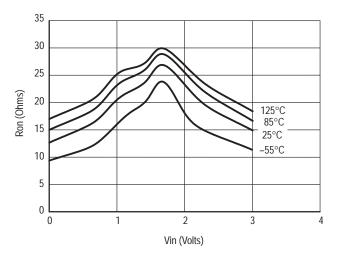
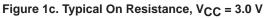


Figure 1a. Typical On Resistance, $V_{CC} = 2.0 \text{ V}$, $T = 25^{\circ}\text{C}$

Figure 1b. Typical On Resistance, V_{CC} = 2.0 V





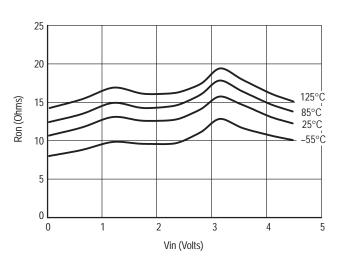


Figure 1d. Typical On Resistance, $V_{CC} = 4.5 \text{ V}$

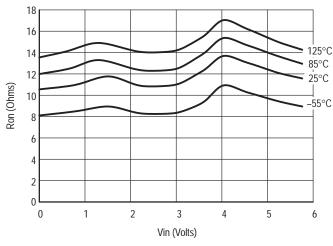


Figure 1e. Typical On Resistance, V_{CC} = 5.5 V

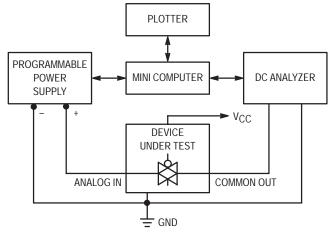


Figure 2. On Resistance Test Set-Up

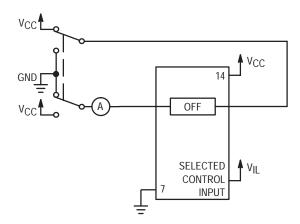


Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

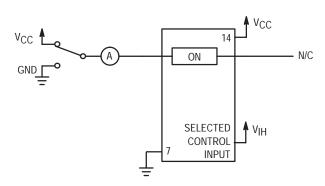
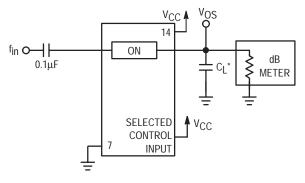
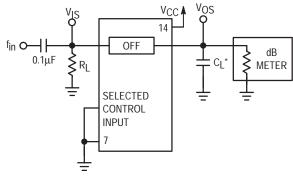


Figure 4. Maximum On Channel Leakage Current, Test Set-Up



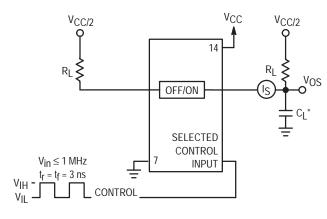
*Includes all probe and jig capacitance.

Figure 5. Maximum On-Channel Bandwidth
Test Set-Up



*Includes all probe and jig capacitance.

Figure 6. Off-Channel Feedthrough Isolation, Test Set-Up



*Includes all probe and jig capacitance.

Figure 7. Feedthrough Noise, ON/OFF Control to Analog Out, Test Set-Up

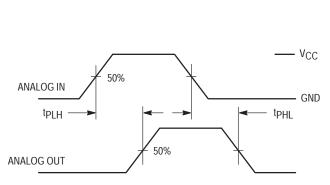
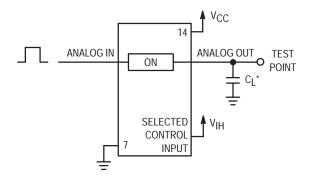
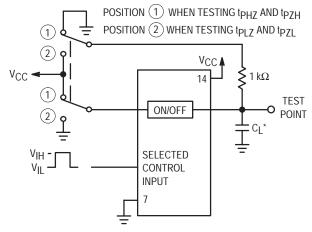


Figure 8. Propagation Delays, Analog In to Analog Out



*Includes all probe and jig capacitance.

Figure 9. Propagation Delay Test Set-Up



*Includes all probe and jig capacitance.

Figure 11. Propagation Delay Test Set-Up

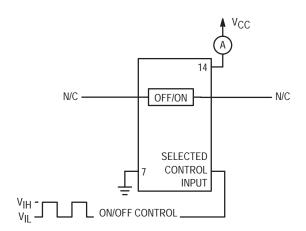


Figure 13. Power Dissipation Capacitance
Test Set-Up

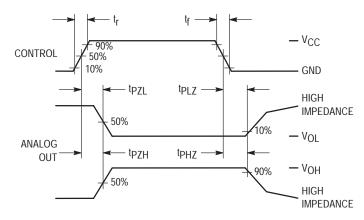
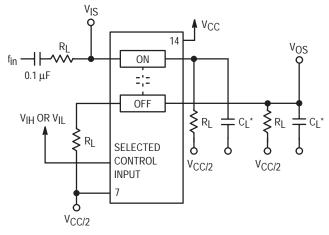
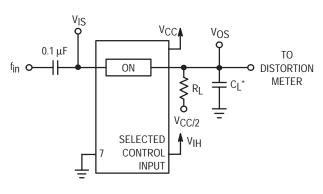


Figure 10. Propagation Delay, ON/OFF Control to Analog Out



*Includes all probe and jig capacitance.

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up



*Includes all probe and jig capacitance.

Figure 14. Total Harmonic Distortion, Test Set-Up

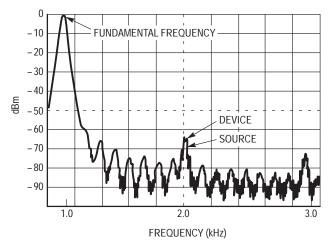


Figure 15. Plot, Harmonic Distortion

APPLICATION INFORMATION

The ON/OFF Control pins should be at V_{IH} or V_{IL} logic levels, V_{IH} being recognized as logic high and V_{IL} being recognized as a logic low. Unused analog inputs/outputs may be left floating (not connected). However, it is advisable to tie unused analog inputs and outputs to V_{CC} or GND through a low value resistor. This minimizes crosstalk and feedthrough noise that may be picked–up by the unused I/O pins.

The maximum analog voltage swings are determined by the supply voltages V_{CC} and GND. The positive peak analog voltage should not exceed V_{CC} . Similarly, the negative peak analog voltage should not go below GND. In the example below, the difference between V_{CC} and GND is six volts.

Therefore, using the configuration in Figure 16, a maximum analog signal of six volts peak—to—peak can be controlled.

When voltage transients above V_{CC} and/or below GND are anticipated on the analog channels, external diodes (Dx) are recommended as shown in Figure 17. These diodes should be small signal, fast turn—on types able to absorb the maximum anticipated current surges during clipping. An alternate method would be to replace the Dx diodes with Mosorbs (MosorbTM is an acronym for high current surge protectors). Mosorbs are fast turn—on devices ideally suited for precise DC protection with no inherent wear out mechanism.

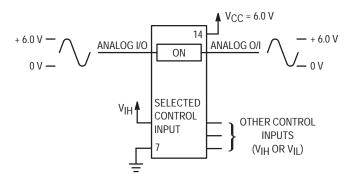


Figure 16. 6.0 V Application

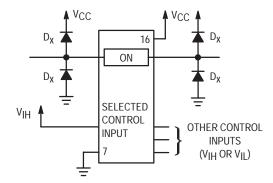


Figure 17. Transient Suppressor Application

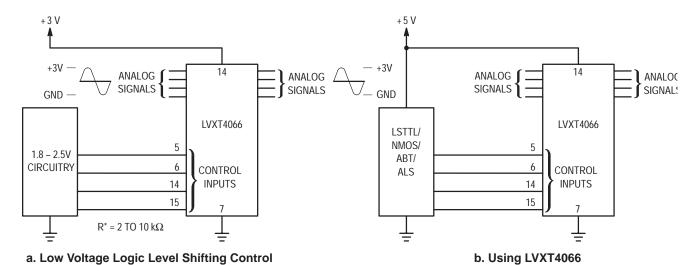


Figure 18. Low Voltage CMOS Interface

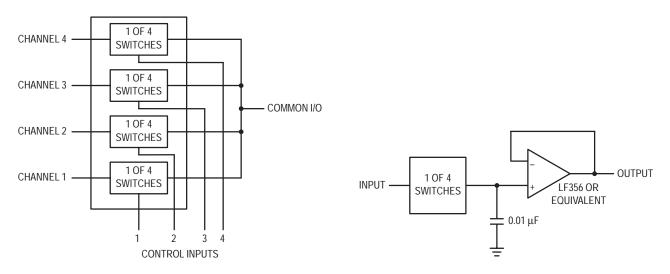
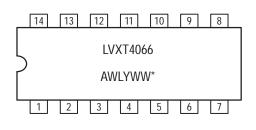


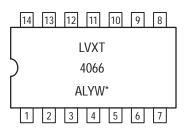
Figure 19. 4-Input Multiplexer

Figure 20. Sample/Hold Amplifier

MARKING DIAGRAMS

(Top View)





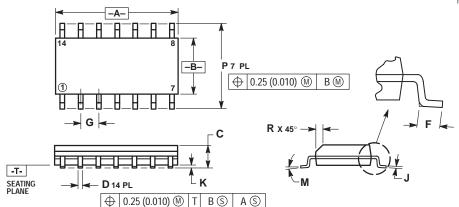
14-LEAD SOIC **D SUFFIX CASE 751A**

14-LEAD TSSOP **DT SUFFIX CASE 948G**

*See Applications Note #AND8004/D for date code and traceability information.

PACKAGE DIMENSIONS

D SUFFIX PLASTIC SOIC PACKAGE CASE 751A-03 ISSUE F



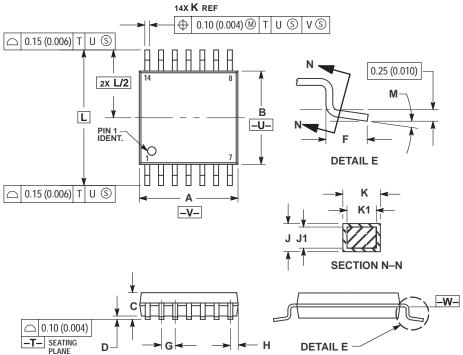
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE
- MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIM	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

DT SUFFIX

PLASTIC TSSOP PACKAGE CASE 948G-01 **ISSUE O**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH,
 PROTRUSIONS OR GATE BURRS. MOLD FLASH
 OR GATE BURRS SHALL NOT EXCEED 0.15
 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD
 FLASH OR PROTRUSION. INTERLEAD FLASH OR
 PROTRUSION SHALL NOT EXCEED
 0.36 (0.010) EEP SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252	BSC	
М	0°	8°	0°	8°	

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